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Erratum: “Copper electroplating for future ultralarge scale integration interconnection” [J. Vac. Sci. Technol. A 18, 656 (2000)]

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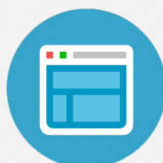
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ERRATA

Erratum: ''Copper electroplating for future ultralarge scale integration interconnection'' [J. Vac. Sci. Technol. A 18, 656 (2000)]

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Due to a delay in mail delivery, the following corrections were not made to my article.
(1) Adding my electronic mail address: my e-mail address is CHUNLIN@CYCU.EDU.TW
(2) On the 4th line of page 657 (right column) mI should be ml in 80–150 ml/l.
(3) On the 18th line of page 659 (left column): but decrease the limiting... should be decreases the limiting...
(4) On the 29th line of page 659 (left column): the dash should be a slash between (111)/(002).
(5) In Fig. 8 caption (page 659); 0.3 □m should be 0.3 μm.
(6) In Fig. 9 caption (page 659); 0.3 □m should be 0.3 μm.
(7) Reference 3 on page 660: please correct to P. Singer, Semicond. Int., June, 1998, p. 91.
(8) Reference 6 on page 660: please correct to P. Andricacos, The Elecrochemical Society Interface, Spring, 1999, p. 32.

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